

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

Claim 1 (original): A method of manufacturing a semiconductor device comprising the steps of:

- forming a semiconductor layer on an insulating surface;
- forming an insulating film on said semiconductor layer;
- forming a first electrode comprising a lamination of a first conductive layer having a first width and a second conductive layer on said insulating film;
- forming a high concentration impurity region in said semiconductor layer by adding an impurity element using said first electrode as a mask;
- forming a second electrode comprising a lamination of said first conductive layer having said first width and a second conductive layer having a second width by etching said second conductive layer of said first electrode;
- forming a third electrode comprising a lamination of a first conductive layer having a third width and said second conductive layer having said second width by etching said first conductive layer of said second electrode; and
- forming a low concentration impurity region in said semiconductor layer by adding an impurity element through said first conductive layer or said insulating film using said second conductive layer as a mask.

Claim 2 (original): The method according to claim 1 wherein said second width is narrower than said first width.

Claim 3 (original): The method according to claim 1 wherein said third width is narrower than said first width and is wider than said second width.

Claim 4 (original): The method according to claim 1 wherein, after a first conductive film and a second conductive film are formed in a lamination on said insulating film, said second conductive layer is formed by performing a first etching process with said second conductive film, and said first conductive layer having said first width is formed by performing a second etching process with said first conductive film, whereby said first electrode comprising a lamination of said first conductive layer having

said first width and said second conductive layer is formed.

Claim 5 (original): The method according to claim 1 wherein said first conductive layer comprises TaN.

Claim 6 (original): The method according to claim 1 wherein said second conductive layer comprises W.

Claim 7 (original): The method according to claim 1 wherein said impurity element comprises phosphorus.

Claim 8 (original): The method according to claim 1 wherein said semiconductor device is an electro-luminescence display device.

Claim 9 (currently amended): The method according to claim 1 wherein said semiconductor device is at least one selected from the group consisting of a video camera, a digital camera, a projector, a goggle-type display, a car navigation system, a personal computer, a player using a recording medium, a mobile computer, an electronic book, and a portable telephone.

Claims 10-18 (canceled)

Claim 19 (original): A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor layer on an insulating surface;

forming an insulating film on said semiconductor layer;

forming a first conductive film and a second conductive film in a lamination on said insulating film;

forming a second conductive layer having a first width by etching said second conductive film;

forming a high concentration impurity region in said semiconductor layer by adding an impurity element through said first conductive film or said insulating film using said second conductive layer having said first width as a mask;

forming a first electrode comprising a lamination of a first conductive layer having a second width and a second conductive layer having a third width by etching said first conductive film;

forming a second electrode comprising a lamination of said first conductive layer having said second width and a second conductive layer having a fourth width by etching said second conductive layer of said first electrode;

forming a third electrode comprising a lamination of a first conductive layer having a fifth width and said second conductive layer having said fourth width by etching said first conductive layer of said second electrode; and

forming a low concentration impurity region in said semiconductor layer by adding an impurity element through said first conductive layer or said insulating film using said second conductive layer having said fourth width as a mask.

Claim 20 (original): The method according to claim 19 wherein said second width is narrower than said first width.

Claim 21 (original): The method according to claim 19 wherein said fifth width is narrower than said second width and is wider than said fourth width.

Claim 22 (original): The method according to claim 19 wherein said first conductive layer comprises TaN.

Claim 23 (original): The method according to claim 19 wherein said second conductive layer comprises W.

Claim 24 (original): The method according to claim 19 wherein said impurity element comprises phosphorus.

Claim 25 (original): The method according to claim 19 wherein said semiconductor device is an electro-luminescence display device.

Claim 26 (currently amended): The method according to claim 19 wherein said semiconductor device is at least one selected from the group consisting of a video camera, a digital camera, a projector, a goggle-type display, a car navigation system, a personal computer, a player using a recording medium, a mobile computer, an electronic book, and a portable telephone.

Claim 27 (original): A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor layer on an insulating surface;

forming an insulating film on said semiconductor layer;

forming a first conductive film and a second conductive film in a lamination on said insulating film;

forming a second conductive layer having a first width by etching said second conductive film;

forming a high concentration impurity region in said semiconductor layer by adding an impurity element through said first conductive film or said insulating film using said second conductive layer having said first width as a mask;

forming a second conductive layer having a second width by etching said second conductive layer;

forming an electrode comprising a lamination of a first conductive layer having a third width and said second conductive layer having said second width by etching said first conductive film; and

forming a low concentration impurity region in said semiconductor layer by adding an impurity element through said first conductive layer or said insulating film using said second conductive layer having said second width as a mask.

Claim 28 (original): The method according to claim 27 wherein said second width is narrower than said first width.

Claim 29 (original): The method according to claim 27 wherein said third width is narrower than said first width and is wider than said second width.

Claim 30 (original): The method according to claim 27 wherein said first conductive layer comprises TaN.

Claim 31 (original): The method according to claim 27 wherein said second conductive layer comprises W.

Claim 32 (original): The method according to claim 27 wherein said impurity element comprises phosphorus.

Claim 33 (original): The method according to claim 27 wherein said semiconductor device is an electro-luminescence display device.

Claim 34 (currently amended): The method according to claim 27 wherein said semiconductor device is at least one selected from the group consisting of a video camera, a digital camera, a projector, a goggle-type display, a car navigation system, a personal computer, a player using a recording medium, a mobile computer, an electronic book, and a portable telephone.

Claim 35 (original): A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor layer on an insulating surface;

forming an insulating film on said semiconductor layer;
forming a first conductive film and a second conductive film in a lamination on said insulating film;
forming a second conductive layer having a first width by etching said second conductive film;
forming a high concentration impurity region in said semiconductor layer by adding an impurity element through said first conductive film or said insulating film using said second conductive layer having said first width as a mask;
forming an electrode comprising a lamination of a first conductive layer having a second width and a second conductive layer having a third width by etching said first conductive film and said second conductive layer; and
forming a low concentration impurity region in said semiconductor layer by adding an impurity element through said first conductive layer or said insulating film using said second conductive layer having said third width as a mask.

Claim 36 (original): The method according to claim 35 wherein said third width is narrower than said first width.

Claim 37 (original): The method according to claim 35 wherein said second width is narrower than said first width and is wider than said third width.

Claim 38 (original): The method according to claim 35 wherein said first conductive layer comprises TaN.

Claim 39 (original): The method according to claim 35 wherein said second conductive layer comprises W.

Claim 40 (original): The method according to claim 35 wherein said impurity element comprises phosphorus.

Claim 41 (original): The method according to claim 35 wherein said semiconductor device is an electro-luminescence display device.

Claim 42 (currently amended): The method according to claim 35 wherein said semiconductor device is at least one selected from the group consisting of a video camera, a digital camera, a projector, a goggle-type display, a car navigation system, a personal computer, a player using a recording medium, a mobile computer, an electronic book, and a portable telephone.

Applicant : Tatsuya Arao et al.
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Amendments to the Drawings:

The attached replacement sheet of drawings includes changes to Fig. 3C and replaces the original sheet including Figs. 3A-3D.

In Figure 3C, the label "v1" has been changed to "W1."

Attachments following last page of this Amendment:

Replacement Sheet (1 page)
Annotated Sheet Showing Change(s) (1 page)